

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SL00F, TC7SL00FU

2-INPUT NAND GATE

The TC7SL00 is a low voltage operative C²MOS 2-INPUT NAND GATE fabricated with silicon gate C²MOS technology.

Operating voltage ($V_{CC(opr)}$) is 1~3V equivalent to 1pc or 2pcs of dry cell battery and it achieves low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

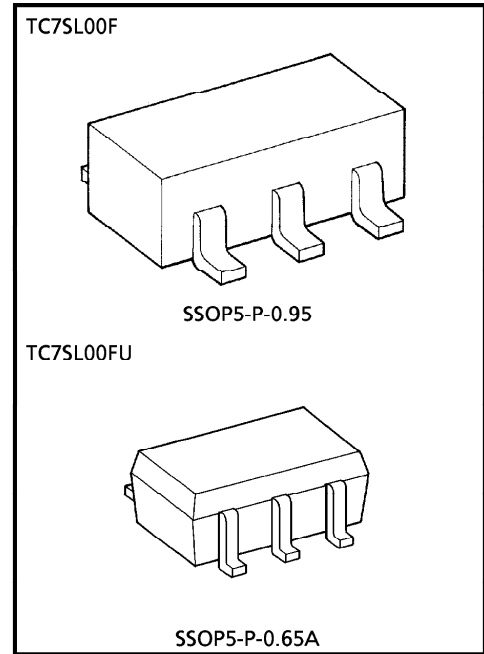
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed $t_{pd} = 10ns$ (Typ.)
at $V_{CC} = 3V$
- Low Power Dissipation $I_{CC} = 1\mu A$ (Max.)
at $T_a = 25^\circ C$
- High Noise Immunity $V_{NIH} = V_{NIL}$
 $= 28\% V_{CC}$ (Min.)
- Symmetrical Output Impedance $|I_{OH}| = I_{OL} = 1mA$
- Balanced Propagation Delay Time $t_{pLH} \cong t_{pHL}$
- Low Voltage Operating $V_{CC(opr)} = 1\sim 3.6V$

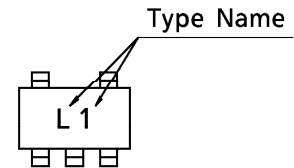
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~5	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 12.5	mA
DC V_{CC} /Ground Current	I_{CC}	± 25	mA
Power Dissipation	P_D	200	mW
Storage Temperature	T_{stg}	-65~150	$^\circ C$
Lead Temperature (10s)	T_l	260	$^\circ C$



Weight SSOP5-P-0.95 : 0.016g (Typ.)
SSOP5-P-0.65A : 0.006g (Typ.)

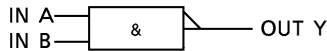
MARKING



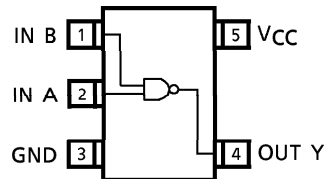
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LOGIC DIAGRAM



PIN CONNECTION (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	1~3.6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	t _r , t _f	0~1000 (V _{CC} = 1.0V)	ns
		0~500 (V _{CC} = 1.5V)	
		0~400 (V _{CC} = 3.0V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT		
				V _{CC}	MIN.	TYP.	MAX.	MIN.		MAX.	
High-Level Input Voltage	V _{IH}	—	—	1.0	0.75	—	—	0.75	—	V	
				1.5	1.05	—	—	1.05	—		
				3.0	2.10	—	—	2.10	—		
Low-Level Input Voltage	V _{IL}	—	—	1.0	—	—	0.25	—	0.25	V	
				1.5	—	—	0.45	—	0.45		
				3.0	—	—	0.90	—	0.90		
High-Level Output Voltage	V _{OH}	—	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20μA	1.0	0.9	1.0	—	0.9	—	V
					1.5	1.4	1.5	—	1.4	—	
					3.0	2.9	3.0	—	2.9	—	
Low-Level Output Voltage	V _{OL}	—	V _{IN} = V _{IH}	I _{OL} = 20μA	1.0	—	0.0	0.1	—	0.1	V
					1.5	—	0.0	0.1	—	0.1	
					3.0	—	0.0	0.1	—	0.1	
Input Leakage Current	I _{IN}	—	V _{IN} = V _{CC} or GND	I _{OH} = -1mA I _{OH} = -2.6mA	1.5	1.07	1.23	—	0.99	—	μA
					3.0	2.61	2.68	—	2.55	—	
					1.5	—	0.23	0.31	—	0.37	
Quiescent Supply Current	I _{CC}	—	V _{IN} = V _{CC} or GND	I _{OL} = 2.6mA	3.0	—	0.23	0.31	—	0.33	μA
					3.6	—	—	±0.1	—	±1.0	
					3.6	—	—	1.0	—	10.0	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, Input $t_r = t_f = 6\text{ns}$, $V_{CC} = 3.3 \pm 0.3\text{V}$)

CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	Ta = 25°C			UNIT
				MIN.	TYP.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	—	—	5.0	9.0	ns
Propagation Delay Time	t_{PLH} t_{PHL}	—	—	—	7.5	13.0	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 25\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

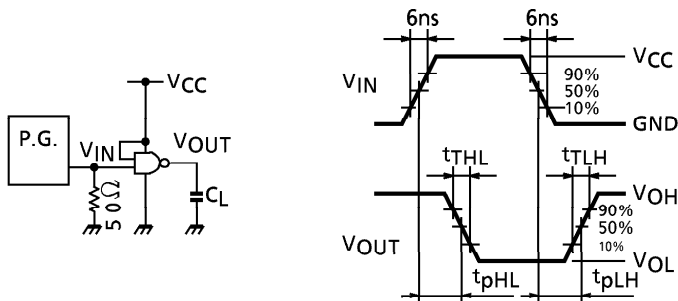
CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	VCC	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	—	1.0	—	70	170	—	240	ns
				1.5	—	25	45	—	55	
				3.0	—	10	15	—	20	
Propagation Delay Time	t_{PLH} t_{PHL}	—	—	1.0	—	70	170	—	210	ns
				1.5	—	25	45	—	55	
				3.0	—	10	15	—	20	
Input Capacitance	C_{IN}	—	—	—	5	10	—	10	pF	
Power Dissipation Capacitance	C_{PD}	—	Note (1)	—	10	—	—	—		

Note (1) : C_{PD} defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

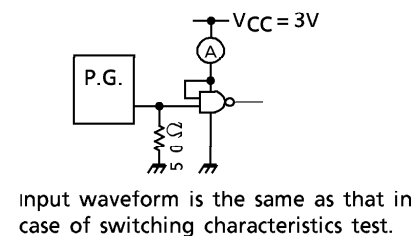
Average operating current can be obtained by the equation as follows.

$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

SWITCHING CHARACTERISTICS TEST CIRCUIT



I_{CC(opr)} TEST CIRCUIT



OUTLINE DRAWING
SSOP5-P-0.95

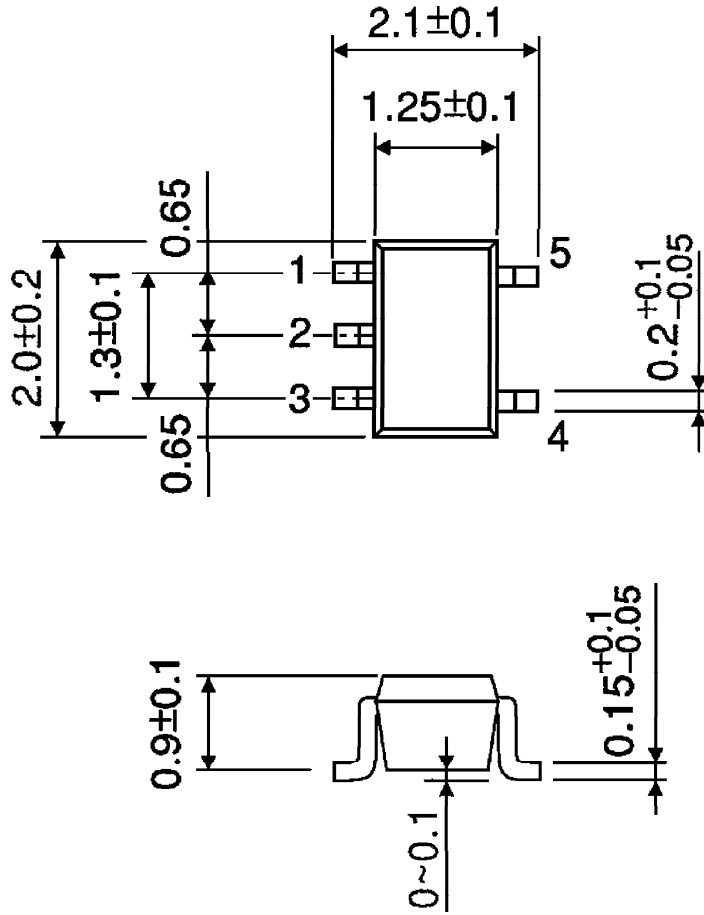
Unit : mm



Weight : 0.016g (Typ.)

OUTLINE DRAWING
SSOP5-P-0.65A

Unit : mm



Weight : 0.006g (Typ.)